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N O I D E L F G H J K L M N O P Q R S T U V W X Y Z						
	Type	Hits	Search Text	DBs	Time Stamp	
Per	1	BRS 0	((gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (fluor\$)))	USPAT	2001/03/19	
Act	2	BRS 1	((gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (fluor\$)))	USPAT	2001/03/19	
Fail	3	BRS 0	((gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (fluor\$)))	EPO; JPO; DERWENT; IBM	2001/03/19	
Save	4	BRS 11	((gate adj insulator) or dielectric) with ((silicon adj oxide) and (nitride or nitrogen) and (fluor\$)))	EPO; JPO; DERWENT; IBM	2001/03/20	
	5	BRS 28	((gate adj insulator) or dielectric) with ((silicon adj oxide) and (nitride or nitrogen) and (fluor\$))) and ((semic	USPAT	2001/03/20	
	6	BRS 17	((gate adj insulator) or dielectric) with ((silicon adj oxide) and (nitride or nitrogen) and (fluor\$))) and ((semi	USPAT	2001/03/20	
	7	BRS 16	halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))	USPAT	2001/03/20	
	8	BRS 1	((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/03/20	
	9	BRS 1	((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/03/20	
	10	BRS 13	(semiconductor adj device) and ((nitrogen adj concentration) with oxynitride)	USPAT	2001/03/20	
	11	BRS 1	((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/03/20	
	12	BRS 11	((halogen with (insulat\$ or dielectric)) and (semiconductor adj device) and (nitrogen with (insulat\$ or dielectric))	USPAT	2001/03/20	
	13	BRS 1	5869858.pn.	USPAT	2001/03/20	
	14	BRS 1	5868930.pn.	USPAT	2001/03/20	
	15	BRS 1	5831319.pn.	USPAT	2001/03/20	
	16	BRS 1	5814863.pn.	USPAT	2001/03/20	
	17	BRS 1	5753564.pn.	USPAT	2001/03/20	
	18	BRS 0	((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and ((insulating or dielectric) adj film)) ab	USPAT	2001/03/20	
	19	BRS 0	((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and ((insulating or dielectric)) ab.	USPAT	2001/03/20	
	20	BRS 0	((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and ((insulating or dielectric)) ctm.	USPAT	2001/03/20	
	21	BRS 0	((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and ((insulating or dielectric))) and (semi	USPAT	2001/03/20	
	22	BRS 0	((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and ((insulating or dielectric))) and (semi	USPAT	2001/03/20	
	23	BRS 8	((halogen with (insulat\$ or dielectric)) and (semiconductor adj device) and (nitrogen with (insulat\$ or dielectric)))	EPO; JPO; DERWENT; IBM	2001/03/20	
	24	BRS 0	(nitrogen adj concentration) with ((insulating or dielectric) adj film)	US-PGPUB	2001/03/20	
	25	BRS 2	(semiconductor adj device) ti.	US-PGPUB	2001/03/20	
	26	BRS 4	((nitrogen adj concentration) with ((insulating or dielectric) adj film)) and (halogen or fluor\$)	USPAT	2001/03/20	
	27	BRS 15	(atomic adj percent) same (atomic adj concentration)	USPAT	2001/03/21	
	28	BRS 1	6191483.pn.	USPAT	2001/03/21	
	29	BRS 25	((gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping)) and (nitrogen with conce	USPAT	2001/09/20	
	30	BRS 1	((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/09/21	
	31	BRS 2	((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	EPO; JPO; DERWENT; IBM	2001/09/21	
	32	BRS 34	((halogen with (insulat\$ or dielectric)) and (semiconductor adj device) and (nitrogen with (insulat\$ or dielectric)))	USPAT	2001/09/21	
	33	BRS 2	((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/09/21	
	34	BRS 2	((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	EPO; JPO; DERWENT; IBM	2001/09/22	
	35	BRS 36	(gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping)	USPAT	2001/09/22	
	36	BRS 36	(gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping)	USPAT	2001/09/22	
	37	BRS 5	((gate adj (insulator or dielectric or insulating)) with (halide or halogen or fluorine or bromine or chlorine or iodi	USPAT	2001/09/23	
	38	BRS 36	((gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping))	USPAT	2001/09/23	
	39	BRS 0	((spacer) with (source or drain)) and ("JP 11111845 A" DID. and (((gate adj insulator) or dielectric) with ((sili	USPAT	2001/09/23	
	40	BRS 0				
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Per	40	BRS 28	((spacer) with (source or drain)) and (((source or drain) with (beside) with (gate)))	USPAT	2001/09/23		
Acti	41	BRS 0	((spacer with (source or drain) with polysilicon) not ((ltd or (lightly adj doped)).ab.)) and ("spacer is drain")	USPAT	2001/09/23		
Fail	42	BRS 0	((spacer with (source or drain) with polysilicon) not ((ltd or (lightly adj doped)).ab.)) and ("spacer is" adj (drai	USPAT	2001/09/23		
Save	43	BRS 18	((lateral with transistor) and (spacer with polysilicon)) not ((bipolar or bjt).ab.)) and ((source or drain) with ab	USPAT	2001/09/23		
	44	BRS 12	((lateral with transistor) and (spacer with polysilicon)) not ((bipolar or bjt).ab.)) and ((source or drain) with ab	USPAT	2001/09/23		
	45	BRS 22	((lateral with transistor) and (spacer with (polysilicon or silicon))) not ((bipolar or bjt).ab.)) and ((source or dr	USPAT	2001/09/23		
	46	BRS 10	((lateral with transistor) and (spacer with (polysilicon or silicon))) not ((bipolar or bjt).ab.)) and ((source or dr	USPAT	2001/09/23		
	47	BRS 0	(polysilicon adj (drain or source) adj spacer)	USPAT	2001/09/23		
	48	BRS 0	(silicon adj (drain or source) adj spacer)	USPAT	2001/09/23		
	49	BRS 26	((silicon adj (drain or source)) with spacer)	USPAT	2001/09/23		
	50	BRS 2	((raised or elevated) adj (source or drain)) not ((soi or (silicon adj on adj insulator)).ab.) and ((polysilicon or s	USPAT	2001/09/23		
	51	BRS 0	(morosawa and narihiro).in.	DERWENT	2001/09/23		
	52	BRS 10	(morosawa).in.	DERWENT	2001/09/23		
	53	BRS 1	3923559.pn.	USPAT	2001/09/23		
	54	BRS 0	((nitrogen with concentration) with ("cm.sub.") with (gate adj (insulation or insulator or dielectric)))	USPAT	2001/09/23		
	55	BRS 33	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric)))	USPAT	2001/09/23		
	56	BRS 0	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric))) same ("cm.sub.")	USPAT	2001/09/23		
	57	BRS 0	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric))) same ("cm.sub.")	USPAT	2001/09/23		
	58	BRS 0	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric))) and ((nitrogen with ("cm.sub.	USPAT	2001/09/23		
	59	BRS 1	6191463.pn. and (concentration)	USPAT	2001/09/23		
	60	BRS 1	6191463.pn. and (nitrogen)	USPAT	2001/09/23		
	61	BRS 1	4016587.pn.	USPAT	2001/09/23		
	62	BRS 23	"4016587"	USPAT	2002/01/14		
	63	BRS 8	(diffusion adj width) and (gate adj width)	USPAT	2002/01/14		
	64	BRS 1	(diffusion adj width) with different	USPAT	2002/01/14		
	65	BRS 1	(diffusion adj width) with (minimize)	USPAT	2002/01/14		
	66	BRS 0	(diffusion adj width) with (minimal)	USPAT	2002/01/14		
	67	BRS 1	(diffusion adj width) with (reduce)	USPAT	2002/01/14		
	68	BRS 1	array and ((diffusion adj width) with (area))	USPAT	2002/01/14		
	69	BRS 10	(diffusion adj width) with (area)	USPAT	2002/01/14		
	70	BRS 7	(diffusion adj width) with (area)	US-PGPUB; EPO; JPO; DE	2002/01/14		
	71	BRS 0	(channel adj width) with (area) with (fox or (field adj (oxide or oxidation))) with (reduce or decrease or minimiz	US-PGPUB; EPO; JPO; DE	2002/01/14		
	72	BRS 3	(channel adj width) with (area) with (fox or (field adj (oxide or oxidation))) with (reduce or decrease or minimiz	USPAT	2002/01/14		
	73	BRS 1	(dense or denser) and ((channel adj width) with (area) with (reduce or decrease or minimize))	USPAT	2002/01/14		
	74	BRS 1	"5053840".PN.	USPAT	2002/01/14		
	75	BRS 1	"4377818".PN.	USPAT	2002/01/14		
	76	BRS 1	"4630085".PN.	USPAT	2002/01/14		
	77	BRS 1	"4763177".PN.	USPAT	2002/01/14		
	78	BRS 20	(integration) and ((channel adj width) with (area) with (reduce or decrease or minimize))	USPAT	2002/01/14		
	79	BRS 0					
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Draw	Type	Hits	Search Text	DBs	Time Stamp		
Per	118	BRS 0	((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("f" or fluorine or fluoride)) and (con	USPAT	2002/03/08		
Act	119	BRS 0	((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("f" or fluorine or fluoride)) and (con	USPAT	2002/03/08		
Fail	120	BRS 0	((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("f" or fluorine or fluoride)) and (con	USPAT	2002/03/08		
Save	121	BRS 0	((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("f" or fluorine or fluoride)) and (nit	USPAT	2002/03/08		
	122	BRS 0	((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("f" or fluorine or fluoride)) and (con	USPAT	2002/03/10		
	123	BRS 15	((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("f" or fluorine or fluoride)) and (con	USPAT	2002/03/10		
	124	BRS 0	10-365861.did.	JPO; DERWENT	2002/03/10		
	125	BRS 0	10365861.did.	JPO; DERWENT	2002/03/10		
	126	BRS 5	(narihiro and morosawa and iwata).in.	JPO	2002/03/10		
	127	BRS 5	(narihiro and morosawa and iwata).in.	JPO	2002/03/10		
	128	BRS 5	(narihiro and morosawa and iwata).in.	JPO; DERWENT	2002/03/10		
	129	BRS 5	(morosawa and iwata).in.	JPO; DERWENT	2002/03/10		
	130	BRS 11	(iwata).in. and (sharp.as.) and nitrogen	JPO; DERWENT	2002/03/10		
	131	BRS 3	(morosawa).in. and (sharp.as.) and nitrogen	JPO; DERWENT	2002/03/10		
	132	BRS 0	(maximum adj concentration) with nitrogen with (gate adj (oxide or dielectric or insulator or insulating or insulat	USPAT	2002/03/10		
	133	BRS 5	(maximum adj concentration) with (gate adj (oxide or dielectric or insulator or insulating or insulation))	USPAT	2002/03/10		
	134	BRS 1	"4085498".PN.	USPAT	2002/03/10		
	135	BRS 1	("4085498"	USPAT	2002/03/10		
	136	BRS 4	("4085498"	USPAT	2002/03/10		
	137	BRS 1	"6013553".PN.	USPAT	2002/03/10		
	138	BRS 1	"6140024".PN.	USPAT	2002/03/10		
	139	BRS 1	"5567638".PN.	USPAT	2002/03/10		
	140	BRS 18	(high adj concentration) with nitrogen with (gate adj (oxide or dielectric or insulator or insulating or insulation))	USPAT	2002/03/10		
	141	BRS 31	"5567638"	USPAT	2002/03/10		
	142	BRS 12	"5567638" and (nitrogen with concentration)	USPAT	2002/03/10		
	143	BRS 5	"5674788" and ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concent	USPAT	2002/03/10		
	144	BRS 1	((((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and	USPAT	2002/03/10		
	145	BRS 35	nitrogen with "1.times.10.sup.21"	USPAT	2002/03/10		
	146	BRS 8	((((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and (USPAT	2002/03/10		
	147	BRS 37	nitrogen with "1.times.10.sup.20"	USPAT	2002/03/10		
	148	BRS 0	((((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and (USPAT	2002/03/10		
	149	BRS 6	((((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and (USPAT	2002/03/10		
	150	BRS 14	((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj implant))	USPAT	2002/03/10		
	151	BRS 4	nitrogen with "1.times.10.sup.22"	USPAT	2002/03/10		
	152	BRS 0	((((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("f" or fluorine or fluori	USPAT	2002/03/10		
	153	BRS 0	((((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("f" or fluorine or fluori	USPAT	2002/03/10		
	154	BRS 0	((((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("f" or fluorine or fluori	USPAT	2002/03/10		
	155	BRS 0	((((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("f" or fluorine or fluori	USPAT	2002/03/10		
	156	BRS 15	"5571734"	USPAT	2002/03/10		
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Per	157	BRS 12	"5571734" and concentration	USPAT	2002/03/10	
Act	158	BRS 8	"5571734" and (concentration with (nitrogen or fluorine))	USPAT	2002/03/10	
Fail	159	BRS 4	("4016587"	USPAT	2002/03/11	
Save	160	BRS 1	(6191463.pn.) and boron	USPAT	2002/03/11	
	161	BRS 1	(6191463.pn.) and nitrogen	USPAT	2002/03/11	
	162	BRS 2	"5674788" and fluorine	USPAT	2002/03/11	
	163	BRS 2	"5674788" and fluorine and nitrogen	USPAT	2002/03/11	
	164	BRS 1	5674788.pn. and thickness	USPAT	2002/03/11	
	165	BRS 5	"5674788" and nm	USPAT	2002/03/11	
	166	BRS 1	5397720.pn.	USPAT	2002/03/11	
	167	BRS 20	"5397720" and (angstrom or nm)	USPAT	2002/03/11	
	168	BRS 11	((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT	2002/09/11	
	169	BRS 8	((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride) and ((gate adj (oxide or insu	USPAT; US-PGPUB	2002/09/11	
	170	BRS 27	((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride)and (fluorine with (channel or	USPAT; US-PGPUB	2002/09/11	
	171	BRS 1	"5940699".PN.	USPAT	2002/09/11	
	172	BRS 22	(fluorine with gate with order)	USPAT; US-PGPUB	2002/09/12	
	173	BRS 27	(fluorine with gate) and (fluorine with (injected or injection))	USPAT; US-PGPUB	2002/09/12	
	174	BRS 8	((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride)and (fluorine with (channel or	USPAT; US-PGPUB	2003/05/07	
	175	BRS 6	(MOROSAWA and NARIHIRO and IWATA and HIROSHI).in.	EPO; JPO; DERWENT; IBM	2003/05/07	
	176	BRS 6	(MOROSAWA and NARIHIRO and IWATA and HIROSHI).in.	EPO; JPO; DERWENT; IBM	2003/05/07	
	177	BRS 15	((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/05/07	
	178	BRS 10	gate with nitrogen with boron with fluorine	USPAT	2003/05/19	
	179	BRS 2	gate with nitrogen with boron with fluorine	EPO; JPO; DERWENT	2003/05/19	
	180	BRS 0	((fet or transistor).ab.) and ((gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (flouri\$)))	USPAT	2003/05/19	
	181	BRS 0	transconductance with boron with diffusion	USPAT	2003/05/19	
	182	BRS 2	((flat adj band) with fluorine) same ((flat adj band) with gate)	USPAT	2003/09/04	
	183	BRS 0	((flat adj band) with fluorine) same ((flat adj band) with gate)	EPO; JPO; DERWENT; IBM	2003/09/04	
	184	BRS 0	((flat adj band) with fluorine) same ((flat adj band) with gate)	EPO; JPO; DERWENT; IBM	2003/09/04	
	185	BRS 2	((flat adj band) with fluorine) same ((flat adj band) with gate)	USPAT	2003/09/04	
	186	BRS 1	((flat adj band) with fluorine) same ((flat adj band) with gate)	US-PGPUB	2003/09/04	
	187	BRS 2	(flat adj band) with fluorine with gate	USPAT	2003/09/04	
	188	BRS 2	(flat adj band) with fluorine with gate	USPAT	2003/09/04	
	189	BRS 1	(flat adj band) with fluorine with gate	US-PGPUB	2003/09/04	
	190	BRS 3	transconductance with fluorine with gate	USPAT	2003/09/04	
	191	BRS 3	transconductance with fluorine with gate	USPAT	2003/09/04	
	192	BRS 0	transconductance with fluorine with gate	US-PGPUB	2003/09/04	
	193	BRS 1	transconductance with boron with gate	USPAT	2003/09/04	
	194	BRS 0	(flat\$1band) with fluorine with gate	USPAT	2003/09/04	
	195	BRS 0	(flat\$1band) with fluorine with gate	USPAT	2003/09/04	
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